

THYRISTOR TETRODE

The BRY39 is a planar p-n-p-n trigger device in a TO-72 metal envelope, intended for use in switching applications such as relay and lamp drivers, sensing network for temperature, etc.

For the applications of the BRY39 as SCS see Handbook Part 3, section SWITCHING TRANSISTORS and as PROGRAMMABLE UNIJUNCTION TRANSISTOR see Handbook Part 3, section SWITCHING TRANSISTORS.

QUICK REFERENCE DATA

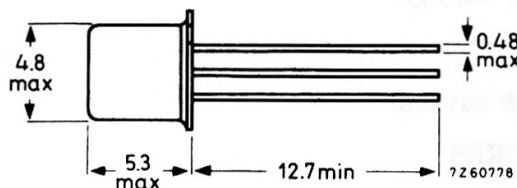
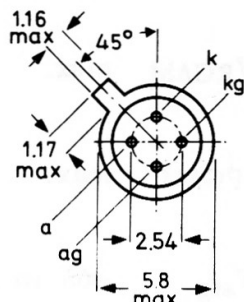
Continuous voltages	$V_D = V_R$	max.	70	V
Repetitive peak voltages	$V_{DRM} = V_{RRM}$	max.	70	V
On-state current up to $T_{case} = 85^\circ C$	I_T	max.	250	mA
Non-repetitive peak on-state current $t = 10 \mu s$; $T_j = 150^\circ C$ prior to surge	I_{TSM}	max.	3	A
Junction temperature	T_j	max.	150	$^\circ C$
Rate of rise of on-state current	$\frac{dI_T}{dt}$	max.	20	A/ μs

MECHANICAL DATA

Dimensions in mm

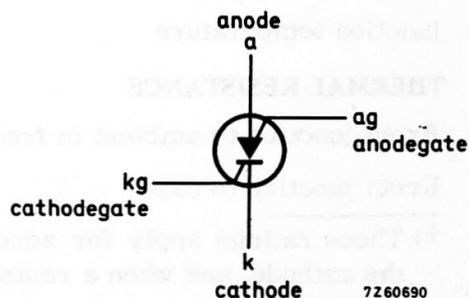
Anodegate connected to case

TO-72



Accessories supplied on request: 56246; 56263

MEANING OF SYMBOLS



RATINGS Limiting values in accordance with the Absolute Maximum System (IEC 134)

ANODE TO CATHODE

Voltages ¹⁾

Continuous voltages	$V_D = V_R$	max.	70	V
Repetitive peak voltages	$V_{DRM} = V_{RRM}$	max.	70	V
Non-repetitive peak voltages	$V_{DSM} = V_{RSM}$	max.	70	V

Currents

On-state current (d. c.) up to $T_{case} = 85\text{ }^{\circ}\text{C}$ up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	I_T	max.	250	mA
	I_T	max.	175	mA
Repetitive peak on-state current $t = 10\text{ }\mu\text{s}; \delta = 0.01$	I_{TRM}	max.	2.5	A
Non-repetitive peak on-state current $t = 10\text{ }\mu\text{s}; T_j = 150\text{ }^{\circ}\text{C}$ prior to surge	I_{TSM}	max.	3	A
Rate of rise of on-state current after triggering to $I_T = 2.5\text{ A}$	$\frac{dI_T}{dt}$	max.	20	A/ μs

CATHODEGATE TO CATHODE www.datasheetcatalog.com

Voltage

Reverse peak voltage	V_{RGKM}	max.	5	V
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Current

Forward peak current	I_{FGKM}	max.	100	mA
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ANODEGATE TO ANODE

Voltage

Reverse peak voltage	V_{RGAM}	max.	70	V
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Current

Forward peak current	I_{FGAM}	max.	100	mA
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TEMPERATURES

Storage temperature	T_{stg}	-65 to +200	$^{\circ}\text{C}$
Junction temperature	T_j	max. 150	$^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\ j-a}$	=	0.45	$^{\circ}\text{C}/\text{mW}$
From junction to case	$R_{th\ j-c}$	=	0.15	$^{\circ}\text{C}/\text{mW}$

1) These ratings apply for zero or negative bias on the cathodegate with respect to the cathode, and when a resistor $R \leq 10\text{ k}\Omega$ is connected between cathodegate and cathode.

CHARACTERISTICSANODE TO CATHODEVoltages

On-state voltage

$I_T = 100 \text{ mA}; T_j = 25^\circ\text{C}$

$V_T < 1.4 \text{ V}$

Rate of rise of off-state voltage

that will not trigger any device ¹⁾

$\frac{dV_D}{dt} 1)$

Currents

Peak reverse current

$V_{RM} = 70 \text{ V}; T_j = 25^\circ\text{C}$

$I_{RM} \begin{matrix} \text{typ.} & 1 & \text{nA} \\ < & 100 & \text{nA} \end{matrix}$

$T_j = 150^\circ\text{C}$

$I_{RM} < 2 \text{ } \mu\text{A}$

Peak off-state current

$V_{DM} = 70 \text{ V}; T_j = 25^\circ\text{C}$

$I_{DM} \begin{matrix} \text{typ.} & 1 & \text{nA} \\ < & 100 & \text{nA} \end{matrix}$

$T_j = 150^\circ\text{C}$

$I_{DM} < 2 \text{ } \mu\text{A}$

Holding current; $R_{GK} = 10 \text{ k}\Omega$; $R_{GA} = 220 \text{ k}\Omega$; $T_j = 25^\circ\text{C}$

$I_H < 250 \text{ } \mu\text{A}$

CATHODEGATE TO CATHODEVoltages

Voltage that will trigger all devices

$V_D = 6 \text{ V}; T_j = 25^\circ\text{C}$

$V_{GKT} > 0.5 \text{ V}$

Current

Current that will trigger all devices

$V_D = 6 \text{ V}; T_j = 25^\circ\text{C}$

$I_{GKT} > 1 \text{ } \mu\text{A}$

ANODEGATE TO ANODEVoltages

Voltage that will trigger all devices

$V_D = 6 \text{ V}; T_j = 25^\circ\text{C}$

$V_{GAT} > 1 \text{ V}$

Current

Current that will trigger all devices

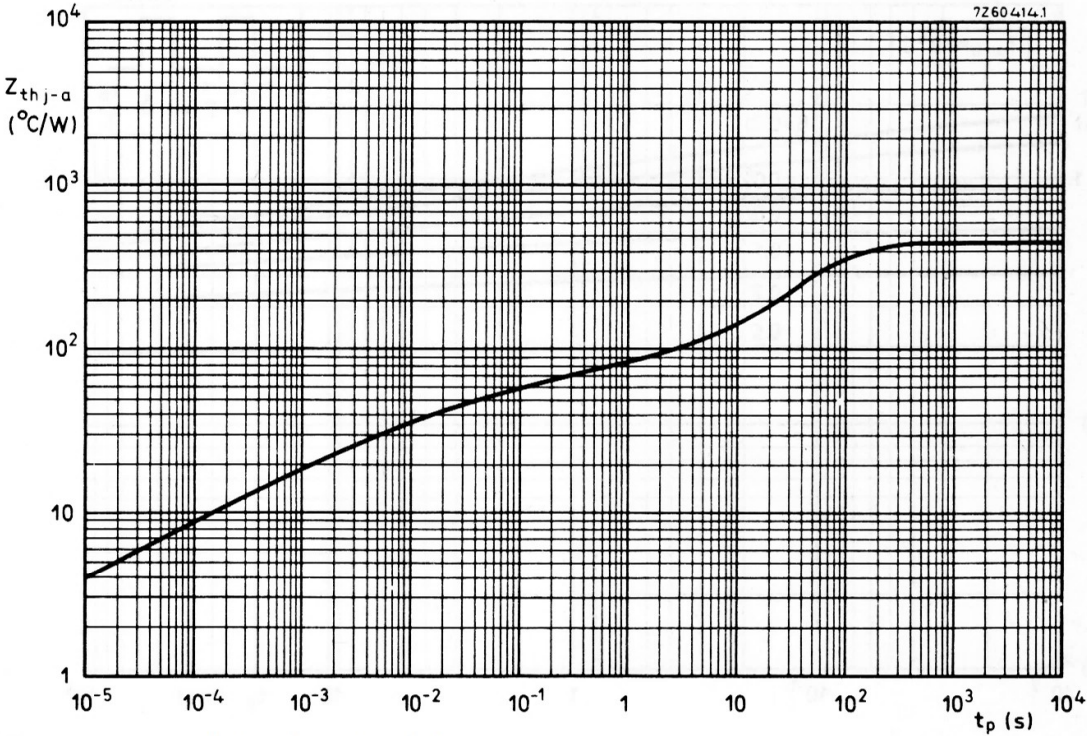
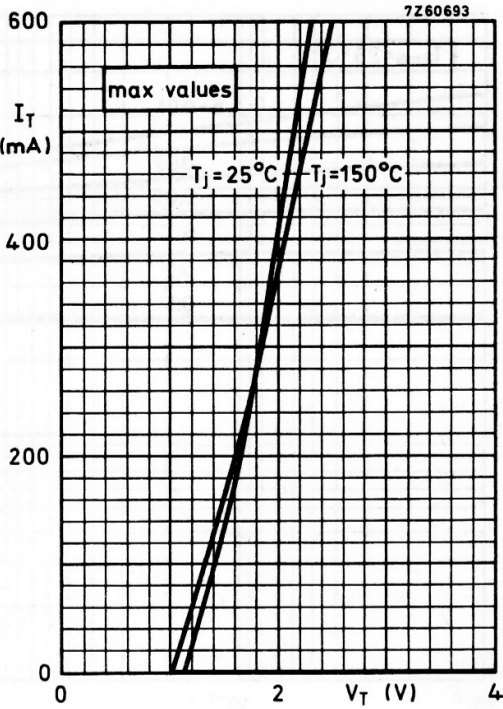
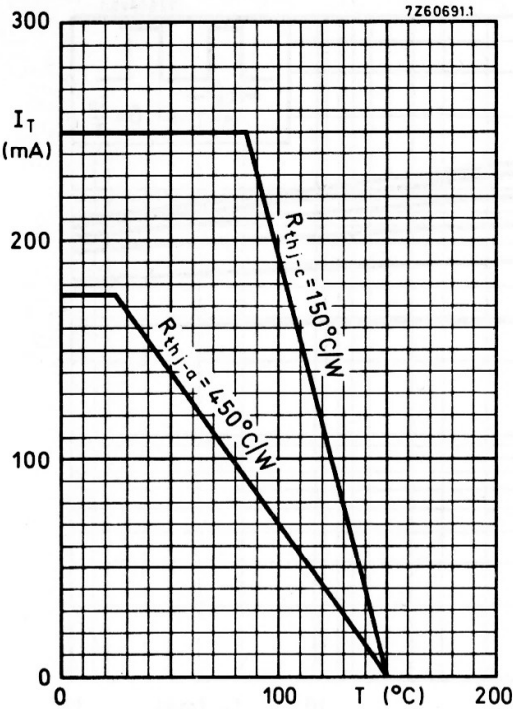
$V_D = 6 \text{ V}; R_{GK} = 10 \text{ k}\Omega; T_j = 25^\circ\text{C}$

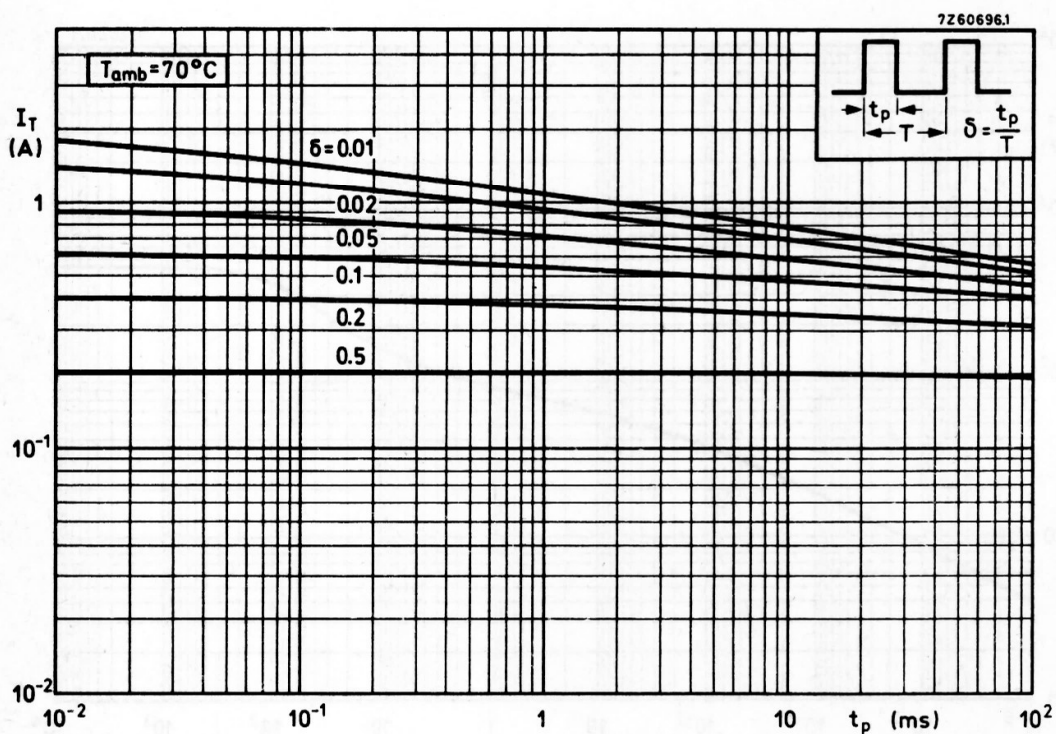
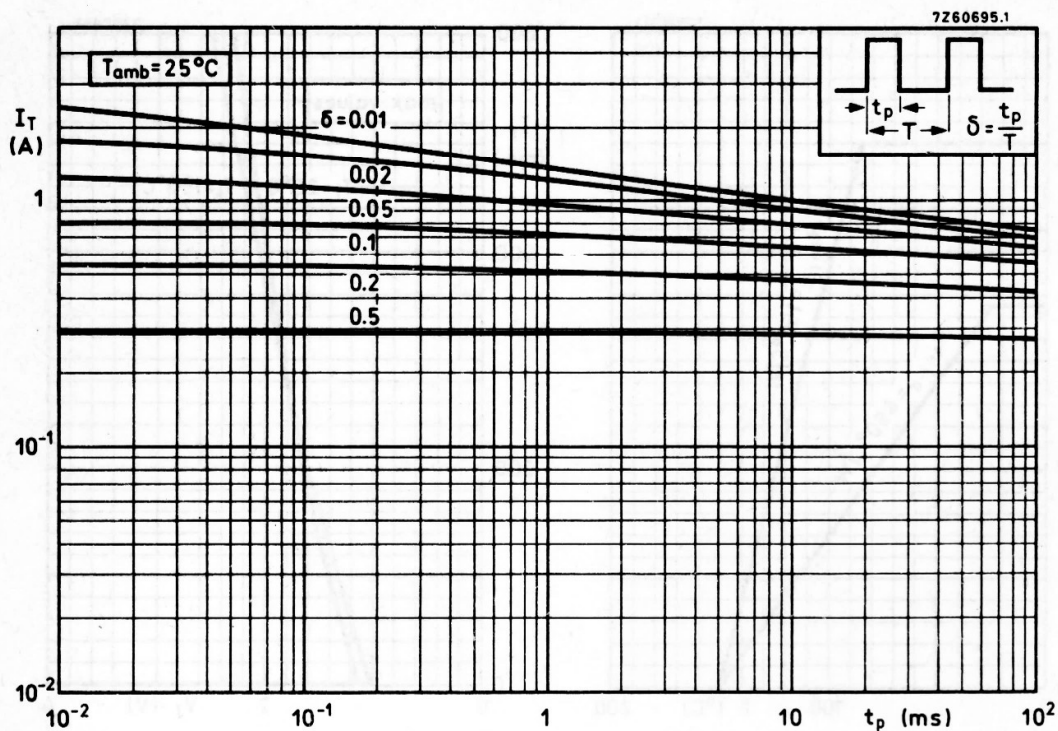
$I_{GAT} > 100 \text{ } \mu\text{A}$

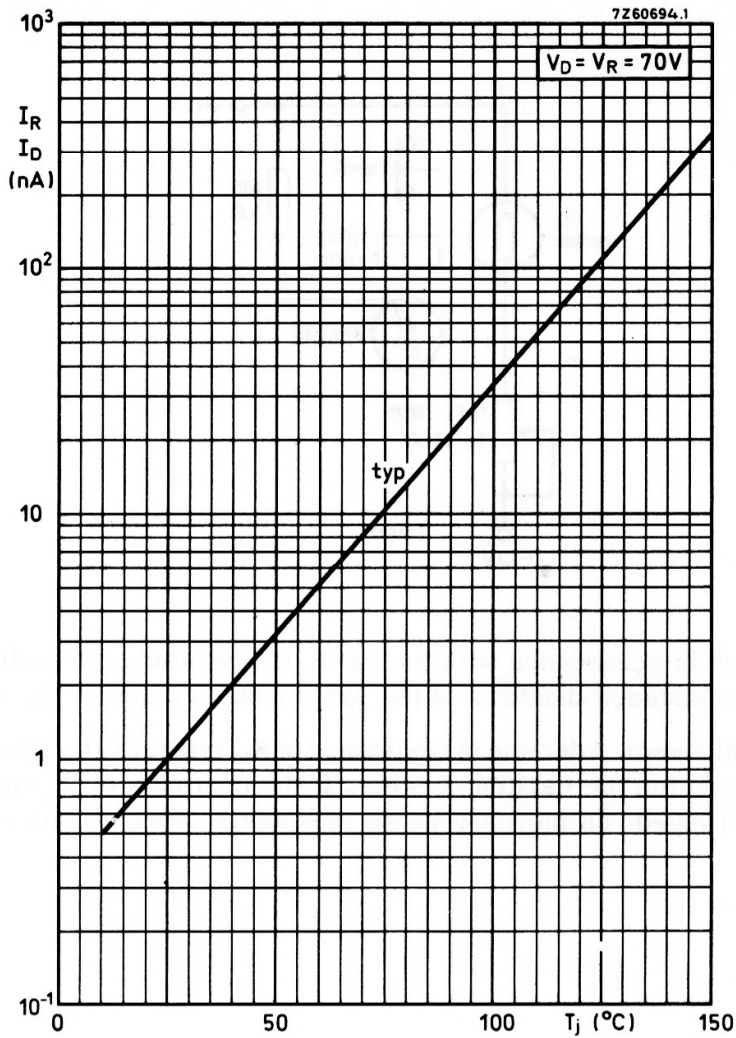
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1) The dV_D/dt is unlimited when the anodegate lead is returned to the anode supply voltage through a current limiting resistor.

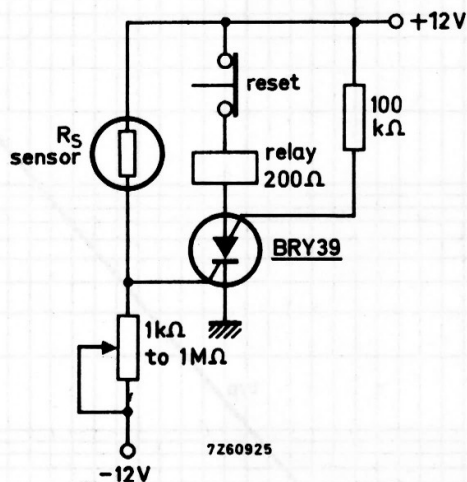
SWITCHING CHARACTERISTICSTurn-on time ($t_{on} = t_d + t_r$) $V_D = 15 \text{ V}; I_T = 150 \text{ mA}$ $R_{GK} = 10 \text{ k}\Omega; T_j = 25 \text{ }^\circ\text{C}$ $t_{on} < 300 \text{ ns}$ Circuit-commutated turn-off time $V_D = V_R = 15 \text{ V}; I_T = 150 \text{ mA}$ $R_{GK} = 10 \text{ k}\Omega; T_j = 25 \text{ }^\circ\text{C}$ $t_{off} < 3 \text{ }\mu\text{s}$







APPLICATION INFORMATION

Sensing network

R_S must be chosen in accordance with the light, temperature, or radiation intensity to be sensed; its resistance should be of the same order as that of the potentiometer.

In the arrangement shown, a decline in resistance of R_S triggers the thyristor, closing the relay that activates the warning system. If the positions of R_S and the potentiometer are interchanged, an increase in the resistance of R_S triggers the thyristor.